UNIKC Semiconductor

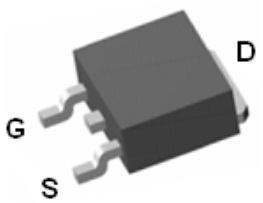
RoHS Compliant

PA110BDA

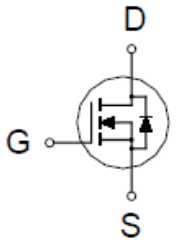
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	105mΩ @V_{GS} = 10V	15A



TO-252



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	15	A
	T_C = 100 °C		9.2	
Pulsed Drain Current[1]		I_{DM}	20	
Avalanche Current		I_{AS}	5.4	
Avalanche Energy	L =1mH	E_{AS}	14.8	mJ
Power Dissipation	T_C = 25 °C	P_D	50	W
	T_C = 100 °C		20	
Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W
Junction-to-Case	$R_{\theta JC}$		2.5	

[1]Pulse width limited by maximum junction temperature.

UNIKC Semiconductor

RoHS Compliant

PA110BDA
N-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.8	3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} = 80V, V_{GS} = 0V, T_J = 125 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 6A		81	120	mΩ
		V_{GS} =10V, I_D = 6A		77	105	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 6A		20		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		592		pF
Output Capacitance	C_{oss}			52		
Reverse Transfer Capacitance	C_{rss}			30		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.3		Ω
Total Gate Charge[2]	Q_g(V_{GS}=10V)	V_{DS} = 50V, I_D = 6A		13.9		nC
	Q_g(V_{GS}=4.5V)			8		
Gate-Source Charge[2]	Q_{gs}			2		
Gate-Drain Charge[2]	Q_{gd}			4.7		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 50V, I_D ≅ 6A, V_{GS} = 10V, R_{GEN} = 6Ω		18		nS
Rise Time[2]	t_r			15		
Turn-Off Delay Time[2]	$t_{d(off)}$			51		
Fall Time[2]	t_f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				15	A
Forward Voltage[1]	V_{SD}	I_F = 6A, V_{GS} = 0V			1.4	V
Reverse Recovery Time	t_{rr}	I_F = 6A, dI/dt = 100A / μS		25		nS
Reverse Recovery Charge	Q_{rr}			25		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

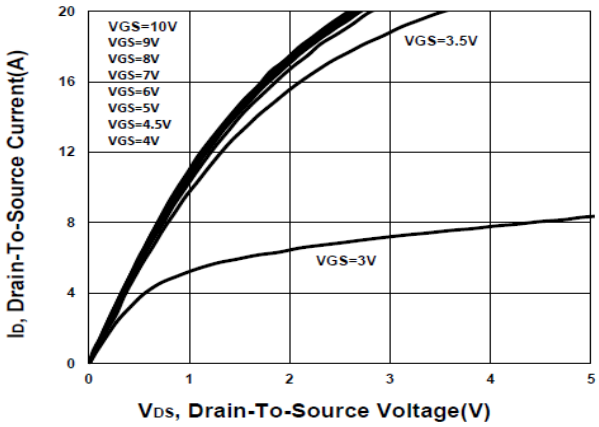
UNIKC Semiconductor

RoHS Compliant

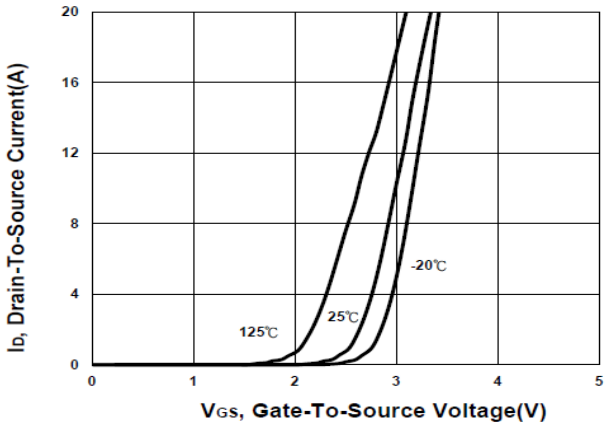
PA110BDA

N-Channel Enhancement Mode MOSFET

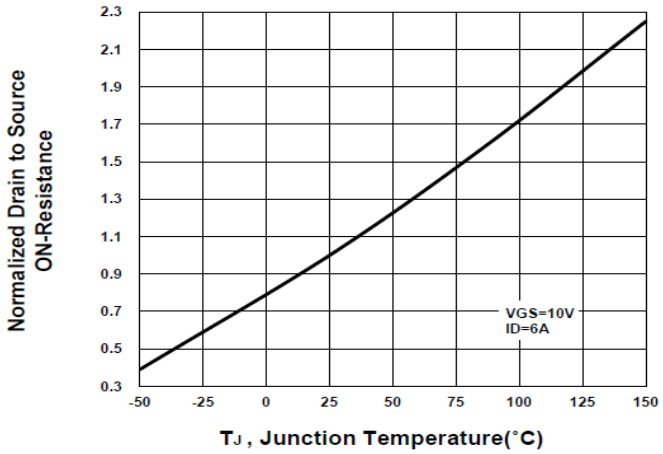
Output Characteristics



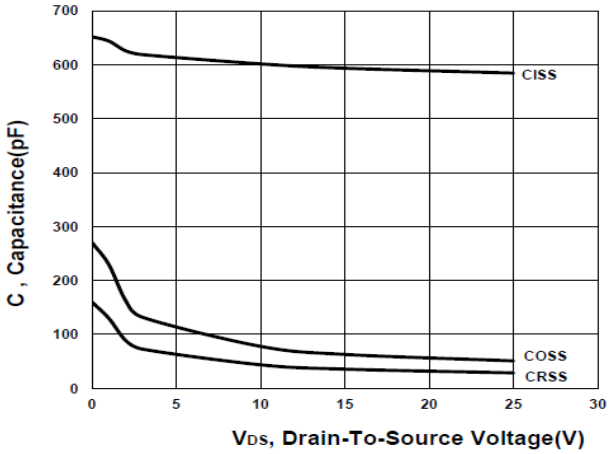
Transfer Characteristics



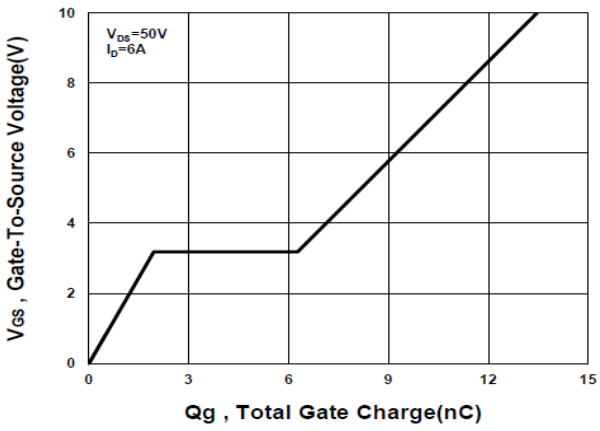
On-Resistance VS Temperature



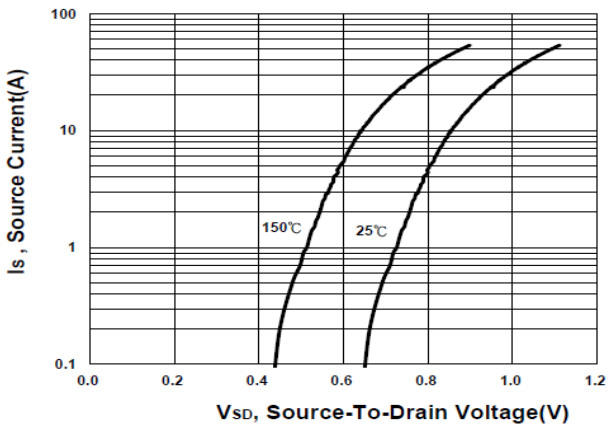
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



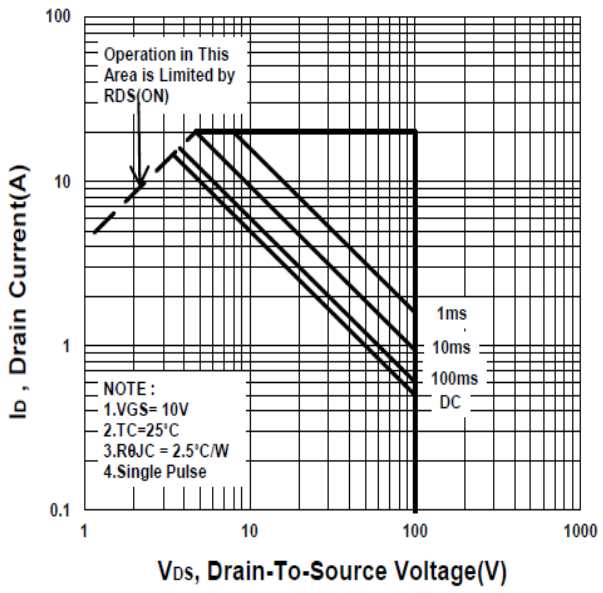
UNIKC Semiconductor

RoHS Compliant

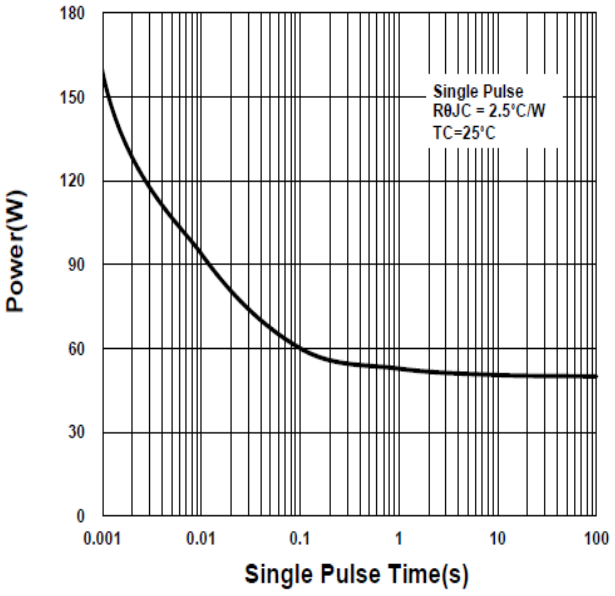
PA110BDA

N-Channel Enhancement Mode MOSFET

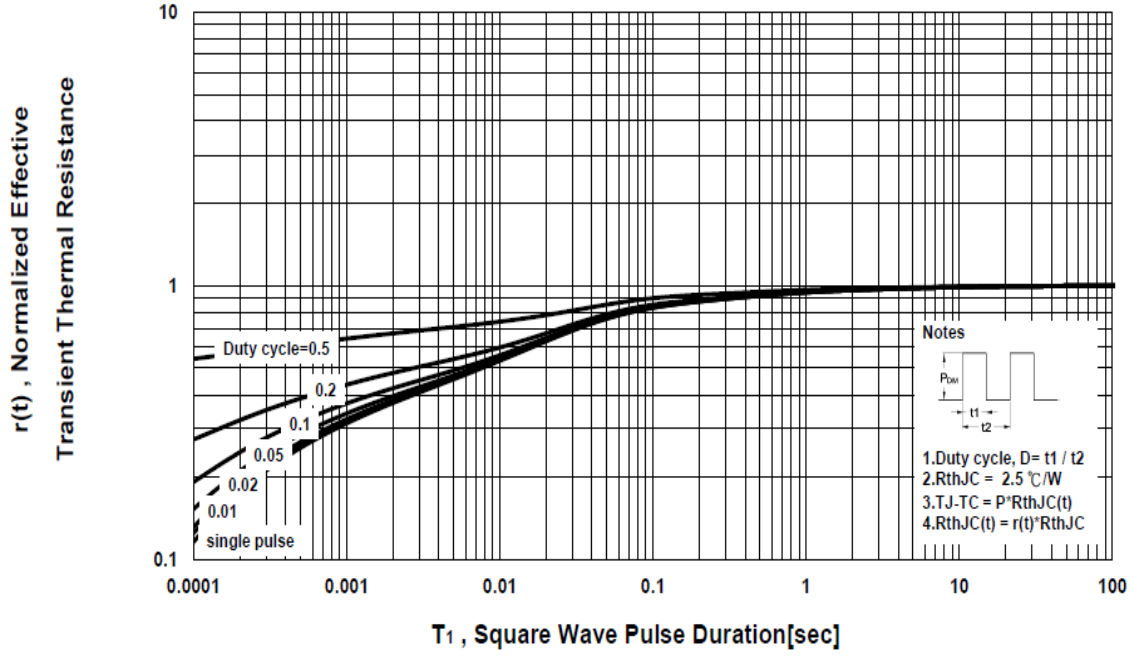
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



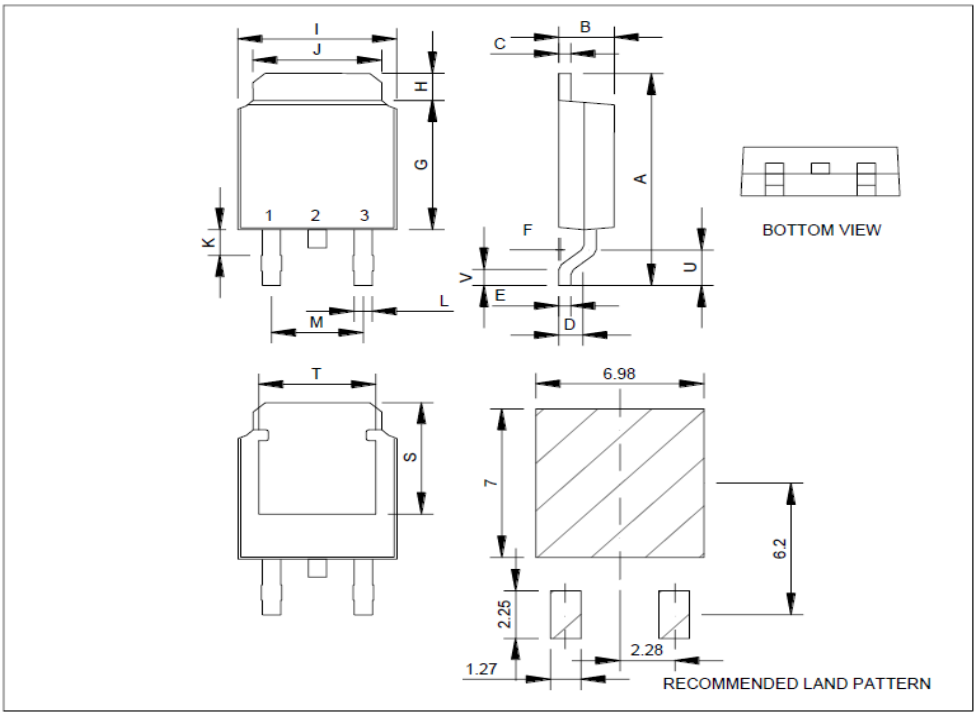
PA110BDA

N-Channel Enhancement Mode MOSFET

Package Dimension

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.4	K	0.15		1.1
C	0.4	0.5	0.61	L	0.4	0.76	0.89
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.4	0.5	0.61	S	4.9	5.1	5.3
F	0		0.2	T	4.6	4.75	5.44
G	5.3	6.1	6.3	U	1.4		1.78
H	0.9		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8				

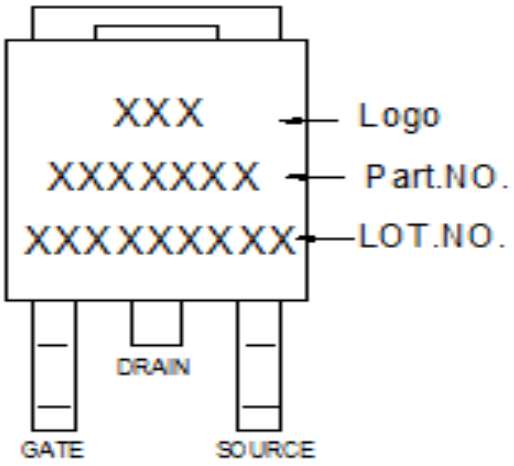


*因为各家封装模具不同而外观略有所差异，不影响电性及Layout。

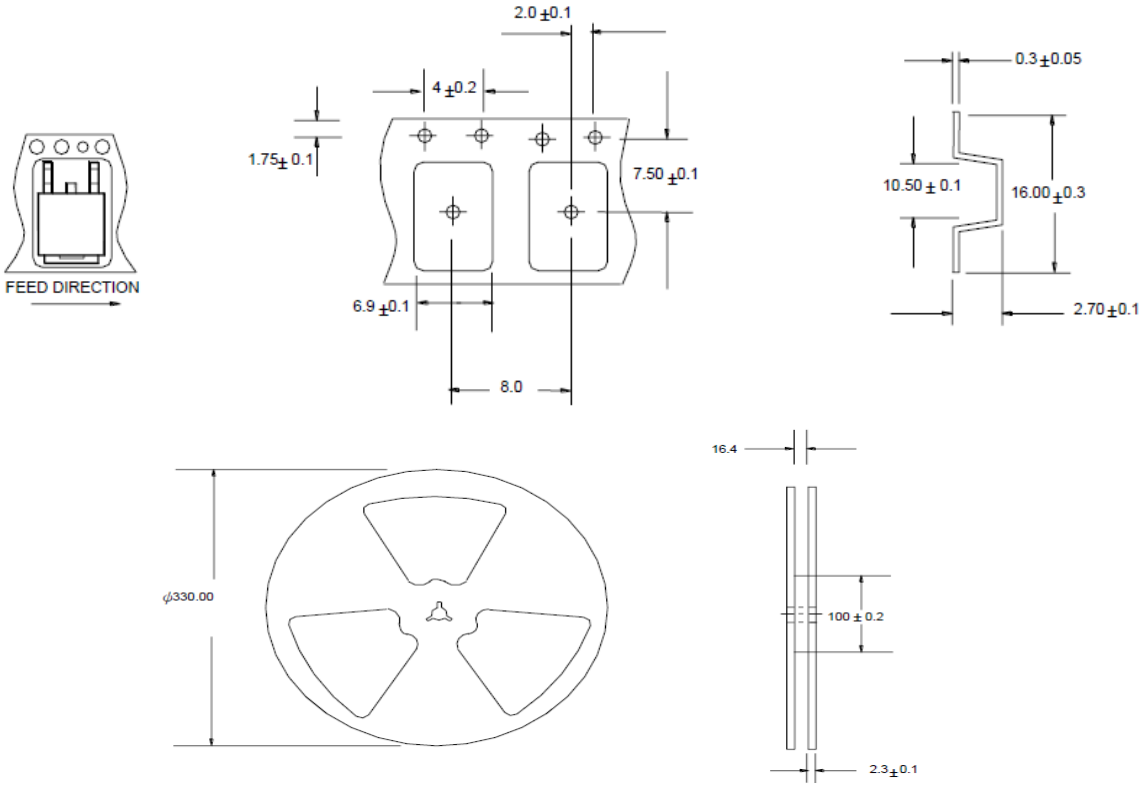
PA110BDA

N-Channel Enhancement Mode MOSFET

A. Marking Information



B. Tape&Reel Information:2500pcs/Reel



UNIKC Semiconductor

RoHS Compliant

PA110BDA

N-Channel Enhancement Mode MOSFET

C. Lot.No. & Date Code rule

1.LOT.NO.

M N 15M21 03

- 03 → #8~9 Sub-lot No
- 15M21 → Order series no.
- N → Foundry site
- M → Assembly site

2.Date Code

D Y M X XXX

- XXX → Order series no. & Sub-lot No
- X → Week
- M → M : Month (A:Jan , B:Feb , C:Mar ,D :Apr ,E:May ,F:Jun,G:Jul,H:Aug,I:Sep,J:Oct,K:Nov,L:Dec.)
- Y → Y : Year (N : 2011, O : 2012 ...)
- D → Assembly site

3.Date Code (for Small package)

XX Y WW

- WW → Week
- Y → Y : Year (9: 2009,A : 2010, B : 2011 ...)
- XX → Device Name

PA110BDA

N-Channel Enhancement Mode MOSFET

D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial （或可区分英文”O”和数字”0”，”G和”Q”的字型即可）
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least